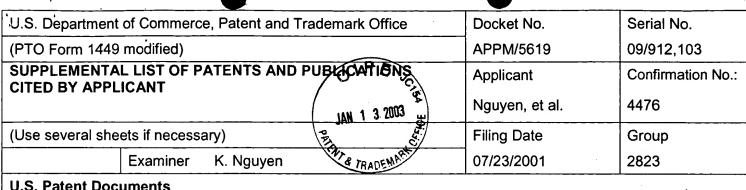


## **U.S. Patent Documents**

*Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
KN.	A1	6,391,790	05/21/2002	Stoehr, et al.	438	715	07/25/2000
KN	A2	6,312,616	11/06/2001	Chinn, et al.	216	68	12/03/1998
KN	А3	6,277,763	08/21/2001	Kugimiyama, et al.	438	720	12/16/1999
KN	A4	6,251,217	06/26/2001	Ye, et al.	156	345	01/27/1999
KN	A5	6,221,784	04/24/2001	Schmidt, et al.	438	719	11/29/1999
ΚN	A6	6,214,637	04/10/2001	Kim, et al.	438	72	04/27/2000
ΚN	A7	6,114,250	09/05/2000	Ellingboe, et al.	438	709	08/17/1998
ΚN	A8	6,080,529	06/27/2000	Ye, et al.	430	318	10/19/1998
KN	A9	6,037,265	03/14/2000	Mui, et al.	438	719	02/12/1998
KN	A10	6,033,979	03/07/2000	Endo	438	622	01/10/1997
KN	A11	6,025,271	02/15/2000	Howard, et al.	438	697	12/08/1997
KN	A12	6,007,732	12/28/1999	Hashimoto, et al.	216	47	05/05/1997
KN	A13	5,994,235	11/30/1999	O'Donnel	438	720	06/24/1998
KW	A14	5,994,160	11/30/1999	Niedermann, et al.	438	53	09/27/1996
KN	A15	5,965,463	10/12/1999	Cui et al.	438	723	07/03/1997
Kn	A16	5,933,729	08/03/1999	Chan	438	257	12/08/1997
الهما	A17	5,900,163	05/04/1999	Yi, et al.	216	79	01/16/1997
KN	A18	5,899,749	05/04/1999	Becker, et al.	438	714	03/18/1997
KN	A19	5,880,033	03/09/1999	Tsai	438	710	06/17/1996
KN	A20	5,854,136	12/29/1998	Huang, et al.	438	714	03/25/1996
ΚN	A21	5,843,847	12/01/1998	Pu, et al.	438	723	04/29/1996
KN	A22	5,773,199	06/30/1998	Linliu, et al.	430	316	09/09/1996
KN	A23	5,767,021	06/16/1998	Imai, et al.	438	719	06/25/1997
KN	A24	5,759,921	06/02/1998	Rostoker	438	711	09/21/1995
KN	A25	5,705,025	01/06/1998	Dietrich, et al.	156	643.1	10/04/1995
Kと	A26	5,658,472	08/19/1997	Bartha, et al.	216	2	06/07/1995
	Examiner Date Considered 62 /12 / 0					idered 62	112/03

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.



U.S. Patent Documer	ıts
---------------------	-----

'Examiner Initial		Document Number	Issue Date	Applicant(s) Name	Class	Subclass	Filing Date If Appropriate
KΝ	A27	5,643,473	07/01/1997	Tachi, et al.	216	67	05/30/1995
K٧	A28	5,571,366	11/05/1996	Ishii, et al.	156	345	10/20/1994
KN	A29	5,486,706	01/23/1996	Yuki, et al.	257	25	05/26/1994
KN	A30	5,458,734	10/17/1995	Tsukamoto	156	643.1	11/01/1994
kN	A31	5,433,823	07/18/1995	Cain	156	662.1	09/30/1993
KN	A32	5,429,070	07/04/1995	Campbell, et al.	118	723 R	11/20/1992
KM	A33	5,358,601	10/25/1994	Cathey	156	656	09/14/1993
kM	A34	5,316,616	05/31/1994	Nakamura, et al.	156	643	05/27/1993
KN	A35	5,242,538	09/07/1993	Hamrah, et al.	156	643	01/29/1992
kN	A36	5,164,330	11/17/1992	Davis, et al.	437	192	04/17/1991
kn	A37	5,110,408	05/05/1992	Fujii, et al.	156	643	02/20/1991
kn	A38	4,741,799	05/03/1988	Chen, et al.	156	643	11/17/1986
KW	A39	4,726,879	02/23/1988	Bondur, et al.	156	643	09/08/1986
KN	A40	4,713,141	12/15/1987	Tsang	156	643	09/22/1986
KW	A41	4,666,555	05/19/1987	Tsang	156	643	08/23/1985
KΝ	A42	4,504,574	03/12/1985	Meyer, et al.	430	331	05/20/1983
KN	A43	4,484,978	11/27/1984	Keyser	156	643	09/23/1983
KM	A44	4,310,380	01/12/1982	Flamm, et al.	156	643	04/07/1980
					-		
Examiner		Khiemmany	24	1	Date Cons	sidered	2/12/03

\*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with your communication to applicant.

U.S. Department of Commerce, Patent and Trademark Office  (PTO Form 1449 modified)  SUPPLEMENTAL LIST OF PATENTS AND PUBLICATIONS  CITED BY APPLICANT					Docket No	Docket No. APPM/5619 Applicant Nguyen, et al. Filing Date		Serial No. 09/912,103 Confirmation No.: 4476 Group	
					APPM/56				
					Applicant				
( JAN 1 3. 2003 gg)				Nguyen, e					
(Use several sheets if necessary)  Examiner K. Nguyen				Filing Date					
		Examiner K. No	guyen	TRADE	07/23/200	1.	2823		
Foreign Pa	atent De	ocuments						-	
*Examiner		Document	Date	Country	Class	Subclass	Transla	ition	
Initial		Number					YES	NO	
Kn	B1	27 01 458 A1	07/21/1977	DE	G03C	5/48			
KN	B2	0 552 491 A1	07/28/1993	EP	H01J	37/32			
ΚN	B3	0 489 407 A2	06/10/1992	EP	H01J	37/32			
KN	B4	09-082,686	03/28/1997	JP	H01L	21/3065	$\boxtimes$		
kΝ	B5	62-181,433	08/08/1987	JP (abs.)	H01L	21/302	$\boxtimes$		
KЧ	B6	60-219,748	11/02/1985	JP (abs.)	H01L	21/302	$\boxtimes$		
KΝ	B7	60-016,422	01/28/1985	JP	C01L	21/30			
KM	B8	01/96955	12/20/2001	WO	G03F	1/00			
,	B9						$\boxtimes$		
	B10						$\boxtimes$		
	B11						$\boxtimes$		
	B12								
	B13						$\boxtimes$		
	B14				-		$\boxtimes$		
	B15			/			$\boxtimes$		
	B16			/			$\boxtimes$		
	B17						$\boxtimes$		
	B18						$\boxtimes$		
	B19						$\boxtimes$		
	B20						$\boxtimes$		
	B21						$\boxtimes$		
	B22								
	B23						$\boxtimes$		
	B 24		/				$\boxtimes$		
Examiner	<del></del>	Khenne		·	Date Cons	sidered o	<u></u>	1	



U.S. Department of Commerce, Patent and Trademark Office			Docket No.	Serial No.			
(PTO Form	1449 п	nodified)	APPM/5619	09/912,103			
SUPPLEM CITED BY		LIST OF PATENTS AND PUBLICATIONS CANT	Applicant  Nguyen, et al.	Confirmation No.:			
(Use sever	al sheet	ts if necessary)	Filing Date	Group			
		Examiner K. Nguyen	07/23/2001	2823			
OTHER AF	RT		· ·	· <del></del>			
*Examiner Initial		Including Author, Title, Date, Pertinent Pages, Etc.		-			
kn	C1	Search Report for PCT/US01/19282, dated May 31, 2002					
KN	C2	Pan, et al., "Selective reactive ion etching of tungsten films in CHF <sub>3</sub> and other fluorinated gases", <i>J. Vac. Sci. and Tech. B</i> , 6(4), (July/August 1988), pp. 1073-1080					
KΝ	С3	Theisen, et al., "Maskless Tungsten Etch Process for Plug Fill", 1046b Extended Abstracts, Electrochem Soc., Spring Meeting, 90(1) (May 6-11, 1990), pp. 248-249					
kn	C4	Ootera, et al., "Highly Selective Etching of W/WN/Poly-Si Gate on Thin Oxide Film With Gaspuff Plasmas", Proc. of Symp.on Dry Process (Nov. 11-12,1999), pp. 155-160					
K12	C5	Hayashi, et al., SiO₂ Etching Using Inductively Coupled Plasma", <i>Electronics &amp; Communications in Japan</i> , Part 2, 81(9) (1998), pp. 21-28					
KV.	C6	Kaplita, et al., "Polysilicon planarization and plug recess etching in decoupled plasma source chamber using two endpoint techniques", The SPIE Conf. on Process, Equipment & Materials Control, Vol. 3882 (Sept. 1999), pp. 90-97					
KN	C7	Khan, et al. "Plasma Etching of Silicon using F USSN 09/263,634.	luorinated Gas Mixtures," I	Filed March 5, 1999			
1.0	C8						
	C9						
	C10	-/					
	C11						
	C12						
	C13						
	C14						
	C15						
Examiner		Whie management	Date Considered	12/12/03			